

#### 1 Characteristics

Table 1. Absolute ratings (limiting values per diode at 25 °C, unless otherwise specified)

Symbol	Parameter	Value	Unit			
$V_{RRM}$	Repetitive peak reverse voltage			170	V	
I <sub>F(RMS)</sub>	Forward rms current			80	Α	
	A	T <sub>c</sub> = 150 °C	Per diode	40		
I <sub>F(AV)</sub>	Average forward current, $\delta$ = 0.5, square wave	T <sub>c</sub> = 140 °C	Per device	80	Α	
I <sub>FSM</sub>	Surge non repetitive forward current	t <sub>p</sub> = 10 ms sinusoidal			Α	
P <sub>ARM</sub>	Repetitive peak avalanche power $t_p = 10 \mu s$ , $T_j = 125 °C$			2750	W	
T <sub>stg</sub>	Storage temperature range			-65 to +175	°C	
Tj	Maximum operating junction temperature (1)			+175	°C	

<sup>1.</sup>  $(dP_{tot}/dT_j) < (1/R_{th(j-a)})$  condition to avoid thermal runaway for a diode on its own heatsink.

Table 2. Thermal resistance parameters

Symbol	Parameter		Max. value	Unit	
R <sub>th(j-c)</sub>	Junction to case	Per diode	0.7	°C/W	
		Total	0.5	C/VV	
R <sub>th(c)</sub>	Coupling		0.3	°C/W	

When the diodes 1 and 2 are used simultaneously:  $\Delta T_{j \text{ (diode1)}} = P_{\text{(diode1)}} \times R_{\text{th(j-c)}}$  (per diode) +  $P_{\text{(diode2)}} \times R_{\text{th(c)}}$ 

For more information, please refer to the following application note:

AN5088: Rectifiers thermal management, handling and mounting recommendations

Table 3. Static electrical characteristics (per diode)

Symbol	Parameter	Test conditions		Min.	Тур.	Max.	Unit
I <sub>R</sub> <sup>(1)</sup>	Reverse leakage current	T <sub>j</sub> = 25 °C	$V_R = V_{RRM}$	-		80	μA
'R\'		T <sub>j</sub> = 125 °C		-	20	80	mA
	Forward voltage drop	T <sub>j</sub> = 25 °C	I <sub>F</sub> = 40 A	-		0.84	V
V <sub>F</sub> <sup>(2)</sup>		T <sub>j</sub> = 125 °C		-	0.68	0.74	
VF (=)		T <sub>j</sub> = 25 °C	I <sub>F</sub> = 80 A	-		0.96	
		T <sub>j</sub> = 125 °C		-	0.80	0.86	

- 1. Pulse test:  $t_p = 5$  ms,  $\delta < 2\%$
- 2. Pulse test:  $t_p$  =380  $\mu$ s,  $\delta$  < 2%

To evaluate the conduction losses, use the following equation:  $P = 0.62 \times I_{F(AV)} + 0.003 \times I_{F}^{2}$  (RMS)

For more information, please refer to the following application notes related to the power losses:

- AN604: Calculation of conduction losses in a power rectifier
- AN4021: Calculation of reverse losses on a power diode

DS4415 - Rev 3 page 2/9



### 1.1 Characteristics (curves)

Figure 1. Average forward power dissipation versus average forward current (per diode)

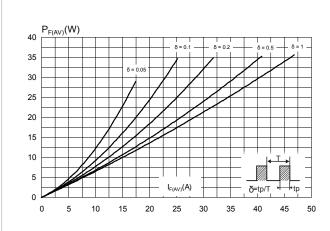


Figure 2. Average forward current versus ambient temperature ( $\delta$  = 0.5, per diode)

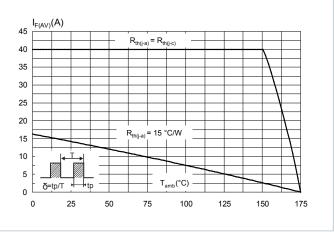


Figure 3. Normalized avalanche power derating versus pulse duration ( $T_i$ = 125 °C)

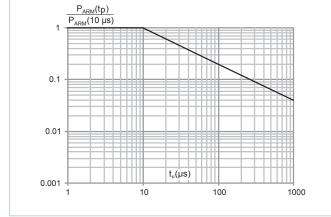
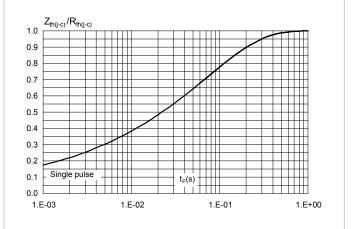


Figure 4. Relative variation of thermal impedance junction to case versus pulse duration



DS4415 - Rev 3 page 3/9



Figure 5. Reverse leakage current versus reverse voltage applied (typical values, per diode)

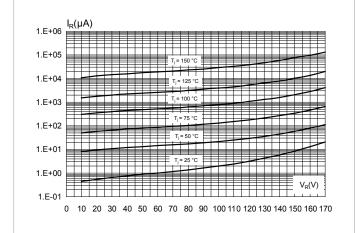


Figure 6. Junction capacitance versus reverse voltage applied (typical values, per diode)

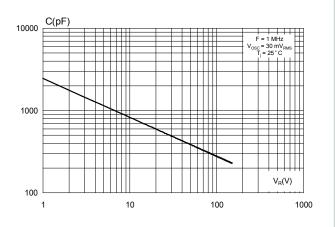


Figure 7. Forward voltage drop versus forward current (per diode, low level)

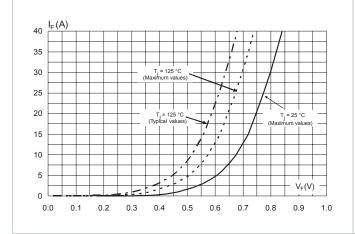
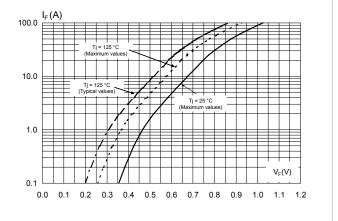


Figure 8. Forward voltage drop versus forward current (per diode, high level)



DS4415 - Rev 3 page 4/9



## 2 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

### 2.1 TO-247 package\_information

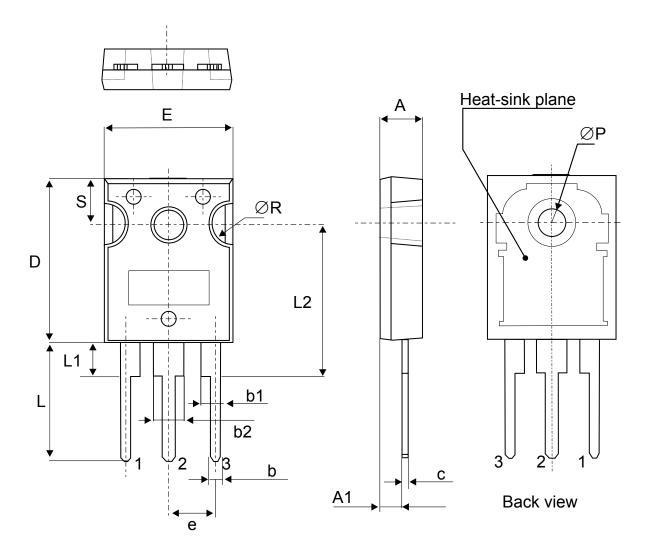
• Epoxy meets UL94, V0

• Cooling method: by conduction (C)

Recommended torque value: 0.8 N·m

Maximum torque value: 1.0 N·m

Figure 9. TO-247 package outline



DS4415 - Rev 3 page 5/9



Table 4. TO-247 package mechanical data

		Dimensions					
Ref.	Millimeters			Inches (for reference only)			
Ī	Min.	Тур.	Max.	Min.	Тур.	Max.	
Α	4.85		5.15	0.191		0.203	
A1	2.20		2.60	0.086		0.102	
b	1.00		1.40	0.039		0.055	
b1	2.00		2.40	0.078		0.094	
b2	3.00		3.40	0.118		0.133	
С	0.40		0.80	0.015		0.031	
D	19.85		20.15	0.781		0.793	
Е	15.45		15.75	0.608		0.620	
е	5.30	5.45	5.60	0.209	0.215	0.220	
L	14.20		14.80	0.559		0.582	
L1	3.70		4.30	0.145		0.169	
L2		18.50			0.728		
ØP	3.55		3.65	0.139		0.143	
ØR	4.50		5.50	0.177		0.217	
S	5.30	5.50	5.70	0.209	0.216	0.224	

DS4415 - Rev 3 page 6/9



# 3 Ordering information

Table 5. Order code

Order code	Marking	Package	Weight	Base qty.	Delivery mode
STPS80170CW	STPS80170CW	TO-247	4.36 g	30	Tube

DS4415 - Rev 3 page 7/9



## **Revision history**

Table 6. Document revision history

Date	Revision	Changes	
16-Sep-2005	1	First issue.	
18-Jan-2018	2	Minor text change to improve readability. Updated Section 2.1: "TO-247 package information".	
09-Aug-2018	3	Updated Table 1. Absolute ratings (limiting values per diode at 25 $^{\circ}$ C, unless otherwise specified) and Figure 3. Normalized avalanche power derating versus pulse duration (T <sub>j</sub> = 125 $^{\circ}$ C).	

DS4415 - Rev 3 page 8/9



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DS4415 - Rev 3 page 9/9